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## Atomic Layer MoS<sub>2</sub> Field-effect Transistors on Hexagonal Boron Nitride Substrate

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The next generation electronics need to not only be smaller but also be more flexible. To meet such demands, electronic devices using two dimensional (2D) atomic crystals like graphene, hexagonal boron nitride (h-BN), molybdenum disulfate (MoS<sub>2</sub>) and organic thin film have been studied intensely. In this talk, I will demonstrate the MoS<sub>2</sub> field effect transistor (FET) toward performance enhancement by insulating h-BN substrate.

**Keywords:** graphene, hexagonal boron nitride (h-BN), molybdenum disulfate (MoS<sub>2</sub>), field effect transistor (FET)